



DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

MPSA92M

TECHNICAL SPECIFICATIONS OF PNP EPITAXIAL PLANAR TRANSISTOR

Description

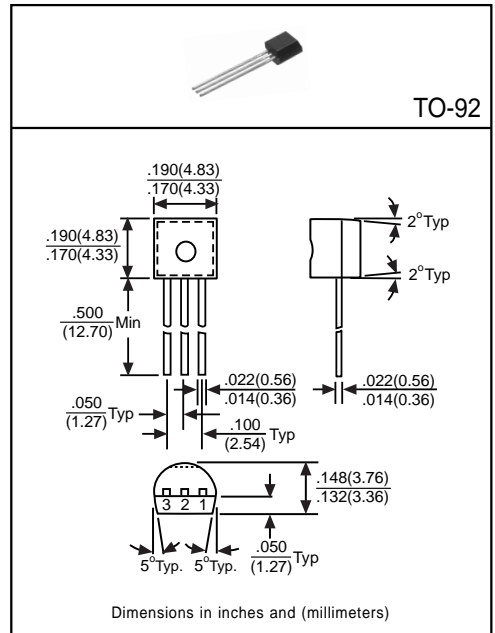
Designed for use as a video output to drive color CRT, or as a dialer circuit in electronic telephone.

Pinning

- 1 = Emitter
- 2 = Base
- 3 = Collector

Absolute Maximum Ratings(T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CBO}	-300	V
Collector-Emitter Voltage	V _{CEO}	-300	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-800	mA
Total Power Dissipation	P _D	625	mW
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-55 to +150	°C



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{CBO}	-300	-	-	V	I _C =-100μA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-300	-	-	V	I _C =-1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	-	-	V	I _E =-10μA, I _C =0
Collector Cutoff Current	I _{CEO}	-	-	-5	μA	V _{CE} =-300V, I _B =0
Emitter Cutoff Current	I _{EBO}	-	-	-0.1	μA	V _{EB} =-3V, I _C =0
Collector-Emitter Saturation Voltage ⁽¹⁾	V _{CE(sat)1}	-	-0.15	-	V	I _C =-30mA, I _B =-1mA
	V _{CE(sat)2}	-	-	-0.7	V	I _C =-100mA, I _B =-10mA
Base-Emitter Saturation Voltage ⁽¹⁾	V _{BE(sat)1}	-	-	-0.9	V	I _C =-20mA, I _B =-2mA
	V _{BE(sat)2}	-	-	-1	V	I _C =-100mA, I _B =-10mA
DC Current Gain ⁽¹⁾	h _{FE1}	80	-	-	-	I _C =-10mA, V _{CE} =-10V
	h _{FE2}	80	-	-	-	I _C =-100mA, V _{CE} =-10V
	h _{FE3}	40	-	-	-	I _C =-200mA, V _{CE} =-10V
Transition Frequency	f _T	50	-	-	MHz	I _C =-10mA, V _{CE} =-20V, f=100MHz

(1)Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%